



Application No. 10/710,012
Customer No. 42717

IFW

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Chien-Chao Huang, et al. § Docket No.: 2001.1531 / 24061.439
Serial No.: 10/710,012 § Examiner: To Be Determined
Filed: June 11, 2004 § Art Unit: 2811
For: Improved Cobalt Silicidation Process for § Conf. No.: 4011
Substrates with a Silicon Germanium Layer §
§

INFORMATION DISCLOSURE STATEMENT

Mail Stop Amendment
Commissioner For Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

In compliance with the duty of disclosure under 37 CFR §1.56, and in accordance with the practice under 37 CFR §1.97 and §1.98, the Examiner's attention is directed to the documents listed on the enclosed modified Form PTO-1449. No inference should be made that the cited references are in fact material, are in fact prior art, or that no better art exists.

The above-identified application was filed after June 30, 2003. Therefore, pursuant to the waiver of the requirement under 37 CFR 1.98 (a)(2)(i) as stated in a Pre-OG Notice dated July 11, 2003, copies of the U.S. patents listed on the enclosed modified Form PTO-1449 are not being provided.

This Information Disclosure Statement is being filed within three months of the United States filing date or before the mailing date of a first Office Action on the merits. No certification or fee is required (37 CFR §1.97(b)).

It is respectfully requested that the above information be considered by the Examiner and that a copy of the enclosed Form PTO-1449 be returned indicating that such information has been considered.

Respectfully submitted,

David M. O'Dell
Registration No. 42,044

Date: February 15, 2005

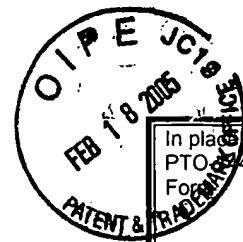
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I hereby certify that this correspondence is being deposited with the United States Postal Service, via First Class Mail to Mail Stop: Patent Application, Commissioner For Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on the February 15, 2005.

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In place of PTO-8949 Form	U. S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>			Application Number	10/710,012	
			Filing Date	June 11, 2004	
			Applicant(s)	Chien-Chao Huang, et al.	
			Art Unit	2811	
			Examiner Name	TBD	
SHEET	1	OF	1	Attorney Docket Number	2001.1531 / 24061.439

U. S. PATENT DOCUMENTS				
Examiner's Initials	Cite No.	Document Number	Publication Date MM-YYYY	Name of Patentee or Applicant of Cited Document
	AA	5,516,724	05-14-1996	Ast, et al.
	AB	5,624,869	04-29-1997	Agnello, et al.
	AC	6,117,723	09-12-2000	Huang
	AD	6,171,959	01-09-2001	Nagabushnam
	AE	6,214,679	04-10-2001	Murthy, et al.
	AF	6,376,342	04-23-2002	Tseng
	AG	6,475,869	11-05-2002	Yu

FOREIGN PATENT DOCUMENTS					
Examiner's Initials	Cite No.	Foreign Patent Document (Country Code - Number - Kind)	Publication Date MM-DD-YYYY	Patentee or Applicant of Cited Document	Translation Y-N

OTHER PRIOR ART		
Examiner's Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article, title of the item, date, page(s), volume-issue number(s), publisher, city-country where published
	AH	GLUCK, M., et al., "CoSi ₂ and TiSi ₂ for Si/SiGe Heterodevices", Elsevier Science S.A., Thin Solid Films 270, 1995, pages 549-554.
	AI	KRIVOKAPIC, Z, et al., "Nickel Silicide Metal Gate FDSOI Devices with Improved Gate Oxide Leakage", IEEE, 2002, 0-7803-7469-X/02, 4 pages.
	AJ	NAYAK, D. K., et al., "Enhancement-Mode Quantum-Well Ge _x Si _{1-x} PMOS, IEEE Electron Device Letters, Vol. 12, No. 4, April 1991, pages 154-156.
	AK	XIANG, QI, et al., "Strained Silicon NMOS with Nickel-Silicide Metal Gate", 2003 Symposium on VLSI Technology Digest of Technical Papers, 4-89114-035-6/03, 2 pages.
	AL	YEO, YEE-CHIA, et al, "Enhanced Performance in Sub-100 nm CMOSFETs Using Strained Epitaxial Silicon-Geranium", IEDM, pages 753-756.

Examiner Signature		Date Considered
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include a copy of this form with next communication to applicant.